TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

2SC1815(L)

Audio Frequency Voltage Amplifier Applications Low Noise Amplifier Applications

• High breakdown voltage, high current capability

: V_{CEO} = 50 V (min), I_C = 150 mA (max)

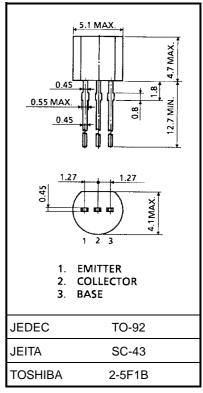
• Excellent linearity of hFE

: hFE (2) = 100 (typ.) at VCE = 6 V, IC = 150 mA

- : $h_{FE} (I_C = 0.1 \text{ mA})/h_{FE} (I_C = 2 \text{ mA}) = 0.95 (typ.)$
- Low noise: NF = 0.2 dB (typ.) (f = 1 kHz).
- Complementary to 2SA1015 (L). (O, Y, GR class).

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	60	V
Collector-emitter voltage	V _{CEO}	50	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	Ι _C	150	mA
Base current	Ι _Β	50	mA
Collector power dissipation	PC	400	mW
Junction temperature	Тj	125	°C
Storage temperature range	T _{stg}	-55~125	°C



Weight: 0.21 g (typ.)

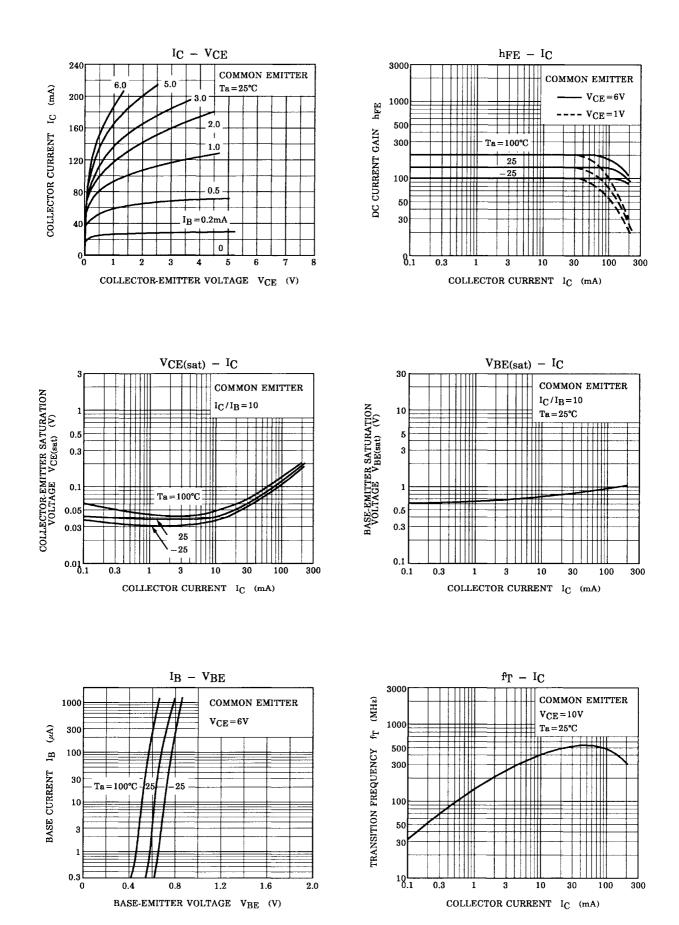
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current		I _{CBO}	$V_{CB} = 60 \text{ V}, \text{ I}_{E} = 0$	_		0.1	μA
Emitter cut-off curre	ent	I _{EBO}	$V_{EB} = 5 V, I_C = 0$	_	_	0.1	μA
DC current gain		h _{FE (1)} (Note)	$V_{CE} = 6 V, I_{C} = 2 mA$	70	_	700	
		h _{FE (2)}	$V_{CE} = 6 \text{ V}, \text{ I}_{C} = 150 \text{ mA}$	25	100	_	
Saturation voltage	Collector-emitter	V _{CE (sat)}	$I_{C} = 100 \text{ mA}, I_{B} = 10 \text{ mA}$	_	0.1	0.25	V
	Base-emitter	V _{BE (sat)}	$I_{C} = 100 \text{ mA}, I_{B} = 10 \text{ mA}$	_	_	1.0	
Transition frequency		f _T	$V_{CE} = 10 \text{ V}, \text{ I}_{C} = 1 \text{ mA}$	80	_	_	MHz
Collector output capacitance		C _{ob}	$V_{CB} = 10 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1 \text{ MHz}$	_	2.0	3.5	pF
Base intrinsic resistance		ľbb'	$V_{CE} = 10 \text{ V}, \text{ I}_{E} = -1 \text{ mA}, \text{ f} = 30 \text{ MHz}$	_	50		Ω
Noise figure		NF (1)	$V_{CE} = 6 \text{ V}, \text{ I}_{C} = 0.1 \text{ mA}$ $R_{G} = 10 \text{ k}\Omega, \text{ f} = 100 \text{ Hz}$		0.5	6	dB
		NF (2)	$V_{CE} = 6 \text{ V}, \text{ I}_{C} = 0.1 \text{ mA}$ $R_{G} = 10 \text{ k}\Omega, \text{ f} = 1 \text{ kHz}$	_	0.2	3	

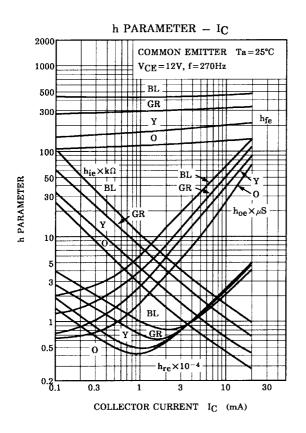
Note: hFE (1) classification O: 70~140, Y: 120~240, GR: 200~400, BL: 350~700

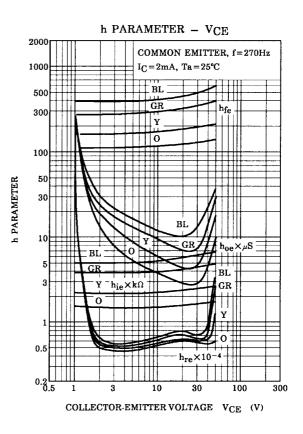
Unit: mm

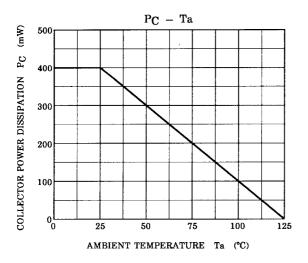
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